# Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

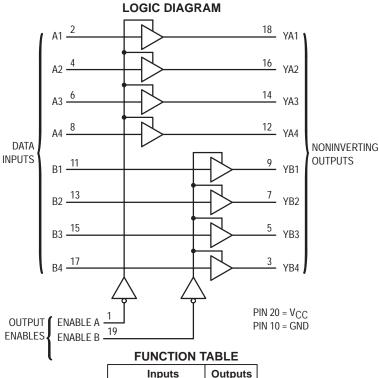
# **High-Performance Silicon-Gate CMOS**

The MC74HC244A is identical in pinout to the LS244. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has noninverting outputs and two active-low output enables.

The HC244A is similar in function to the HC240A.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 136 FETs or 34 Equivalent Gates

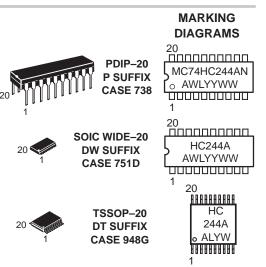


Inpu	Outputs				
Enable A, Enable B	A, B	YA, YB			
L	L	L			
L	Н	Н			
Н	Χ	Z			
Z = high impedance					



### **ON Semiconductor**

http://onsemi.com



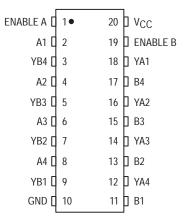
A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

#### **PIN ASSIGNMENT**



#### **ORDERING INFORMATION**

Device	Package	Shipping				
MC74HC244AN	PDIP-20	1440 / Box				
MC74HC244ADW	SOIC-WIDE	38 / Rail				
MC74HC244ADWR2	SOIC-WIDE	1000 / Reel				
MC74HC244ADT	TSSOP-20	75 / Rail				
MC74HC244ADTR2	TSSOP-20	2500 / Reel				

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package:  $-\,7$  mW/°C from  $65^{\circ}$  to  $125^{\circ}C$ 

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		0	Vcc	V
TA	Operating Temperature, All Package Types		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	0 0 0	1000 500 400	ns

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{\text{out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{out}}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{\text{out}} = 0.1 \text{ V}$ $ I_{\text{out}}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
VOH	Minimum High–Level Output Voltage	$V_{\text{in}} = V_{\text{IH}}$ $ I_{\text{out}}  \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{in} = V_{IH} &  I_{out}  \leq 2.4 \text{ r} \\  I_{out}  \leq 6.0 \text{ r} \\  I_{out}  \leq 7.8 \text{ r} \end{aligned} $	nA 4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
VOL	Maximum Low–Level Output Voltage	$V_{\text{in}} = V_{\text{IL}}$ $ I_{\text{out}}  \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{aligned} V_{\text{in}} = V_{\text{IL}} &  I_{\text{out}}  \leq 2.4  \text{r} \\  I_{\text{out}}  \leq 6.0  \text{r} \\  I_{\text{out}}  \leq 7.8  \text{r} \end{aligned}$	nA 4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	

<sup>\*</sup>Maximum Ratings are those values beyond which damage to the device may occur.

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	± 0.5	± 5.0	± 10	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

NOTE: Information on typical parametric values and high frequency or heavy load considerations can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### AC ELECTRICAL CHARACTERISTICS ( $C_L = 50$ pF, Input $t_f = t_f = 6$ ns)

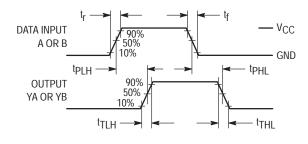
			Guaranteed Limit			
Symbol	Parameter	v <sub>CC</sub>	– 55 to 25°C	≤85°C	≤125°C	Unit
tPLH, tPHL	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	2.0 3.0 4.5 6.0	96 50 18 15	115 60 23 20	135 70 27 23	ns
tPLZ, tPHZ	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
tPZL, tPZH	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High–Impedance State)		15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
СРЕ	Power Dissipation Capacitance (Per Buffer)*	34	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

#### **SWITCHING WAVEFORMS**



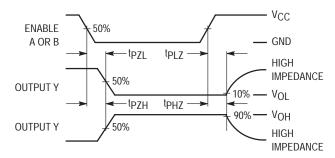
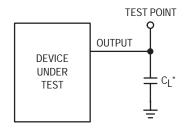


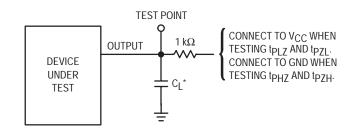
Figure 1.

Figure 2.

#### **TEST CIRCUITS**



\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit

#### **PIN DESCRIPTIONS**

#### **INPUTS**

A1, A2, A3, A4, B1, B2, B3, B4 (Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in noninverted form on the corresponding Y outputs, when the outputs are enabled.

#### **CONTROLS**

#### Enable A, Enable B (Pins 1, 19)

Output enables (active-low). When a low level is applied to these pins, the outputs are enabled and the devices

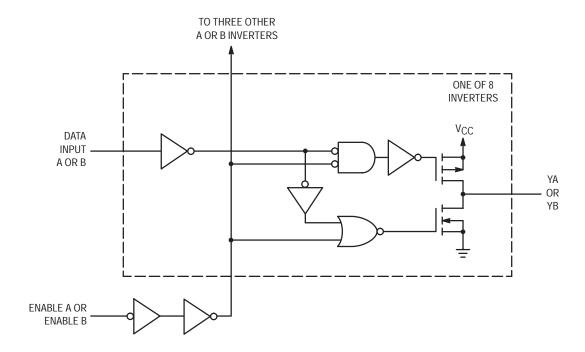
function as noninverting buffers. When a high level is applied, the outputs assume the high impedance state.

#### **OUTPUTS**

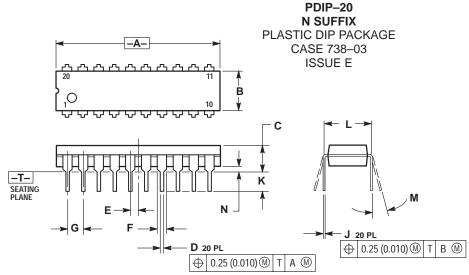
YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pins 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output-enable pins, these outputs are either noninverting outputs or high-impedance outputs.

### **LOGIC DETAIL**



#### **PACKAGE DIMENSIONS**



#### NOTES:

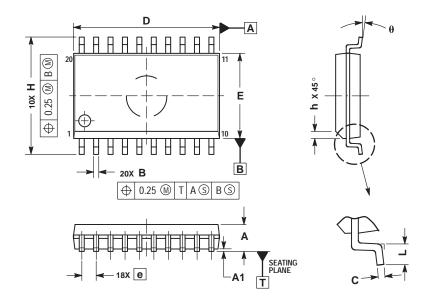
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 1 14.3W, 1702.

  CONTROLLING DIMENSION: INCH.

  DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Ε	0.050	) BSC	1.27	BSC	
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300	) BSC	7.62 BSC		
M	0 °	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

#### SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

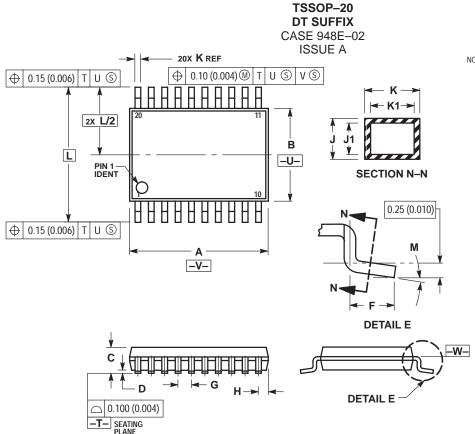
- PER ASME 174-5M, 1994.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
Δ.	0.0	7.0			

#### **PACKAGE DIMENSIONS**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.06) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W—.

	NAIL L IN	METERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affliliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### **PUBLICATION ORDERING INFORMATION**

#### NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

**Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303-308-7140 (M-F 1:00pm to 5:00pm Munich Time)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

**English Phone**: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS\*: 00-800-4422-3781

 ${\rm *Available\ from\ Germany,\ France,\ Italy,\ England,\ Ireland}$ 

#### CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

**Phone**: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

**Phone**: 81–3–5740–2745 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.